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#### What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

#### Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

Ξ·ΧΕΙ

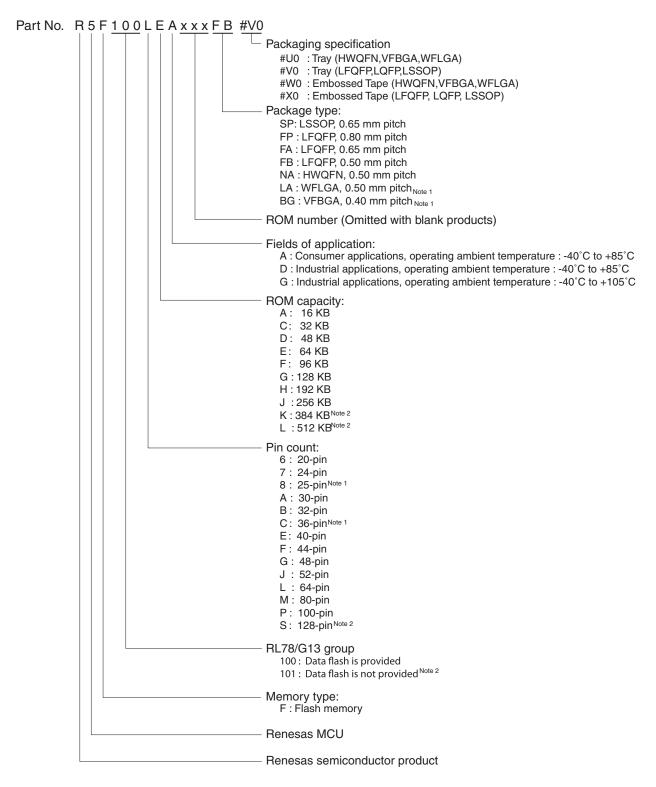
Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I <sup>2</sup> C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	192KB (192K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100lhdfb-v0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

# 1.2 List of Part Numbers





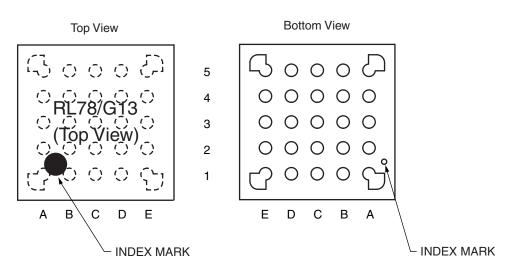
- **Notes** 1. Products only for "A: Consumer applications ( $T_A = -40$  to  $+85^{\circ}C$ )", and "G: Industrial applications ( $T_A = -40$  to  $+105^{\circ}C$ )"
  - **2.** Products only for "A: Consumer applications ( $T_A = -40$  to  $+85^{\circ}C$ )", and "D: Industrial applications ( $T_A = -40$  to  $+85^{\circ}C$ )"



# 1.3.3 25-pin products

• 25-pin plastic WFLGA (3 × 3 mm, 0.50 mm pitch)





	А	В	С	D	E	_
5	P40/TOOL0	RESET	P01/ANI16/ TO00/RxD1	P22/ANI2	P147/ANI18	5
4	P122/X2/ EXCLK	P137/INTP0	P00/ANI17/ TI00/TxD1	P21/ANI1/ AVrefm	P10/SCK00/ SCL00	4
3	P121/X1	Vdd	P20/ANI0/ AV <sub>REFP</sub>	P12/SO00/ TxD0/ TOOLTxD	P11/SI00/ RxD0/ TOOLRxD/ SDA00	3
2	REGC	Vss	P30/INTP3/ SCK11/SCL11	P17/Tl02/ TO02/SO11	P50/INTP1/ SI11/SDA11	2
1	P60/SCLA0	P61/SDAA0	P31/TI03/ TO03/INTP4/ PCLBUZ0	P16/TI01/ TO01/INTP5	P130	1
	А	В	С	D	E	

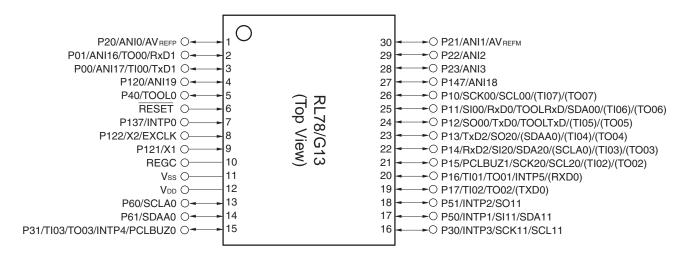
#### Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 $\mu$ F).

**Remark** For pin identification, see **1.4 Pin Identification**.



# 1.3.4 30-pin products

• 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)

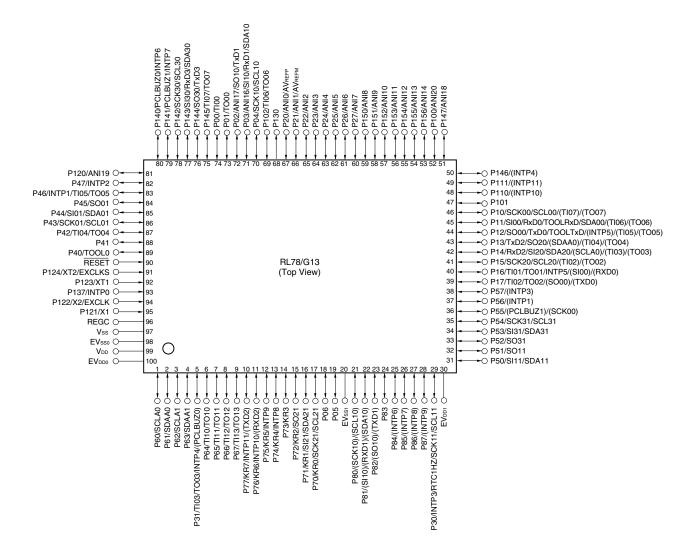


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1  $\mu$ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.





Cautions 1. Make EVsso, EVss1 pins the same potential as Vss pin.

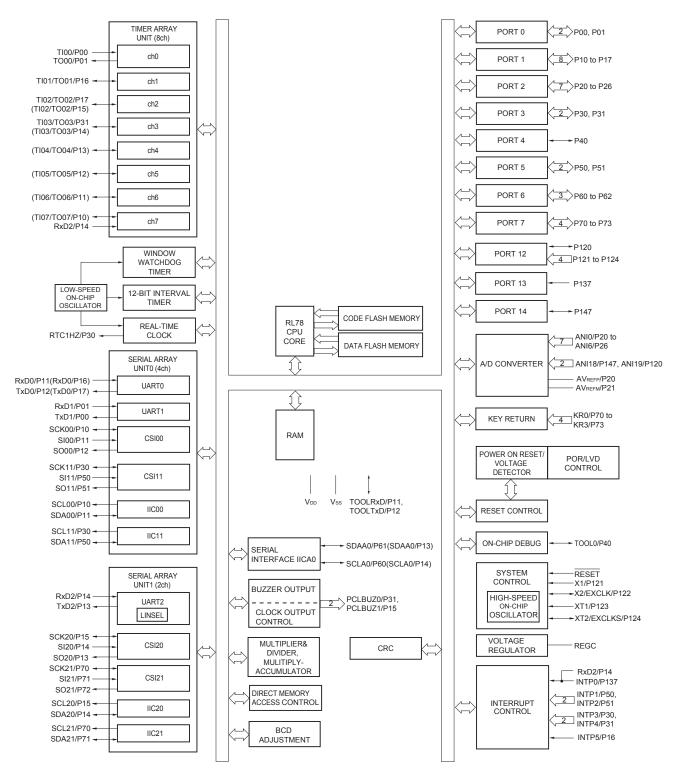
- 2. Make VDD pin the potential that is higher than EVDD0, EVDD1 pins (EVDD0 = EVDD1).
- 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1  $\mu$ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD, EVDD0 and EVDD1 pins and connect the Vss, EVss0 and EVss1 pins to separate ground lines.
- **3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register** (**PIOR**) in the RL78/G13 User's Manual.



# 1.5.7 40-pin products



**Remark** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Юн1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-40	mA
		Total of all pins –170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	-70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	Iol1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
		P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147		100	mA
	IOL2	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins	] [	5	mA
Operating ambient	TA	In normal operati	on mode	-40 to +85	°C
temperature		In flash memory	programming mode		
Storage temperature	Tstg			-65 to +150	°C

# Absolute Maximum Ratings (TA = 25°C) (2/2)

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



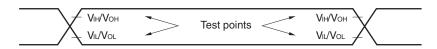
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147		0.8EVDD0		EVDDO	V
	VIH2	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer $4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	2.2		EVDDO	V
		P80, P81, P142, P143	TTL input buffer $3.3 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}$	2.0		EVDDO	V
			TTL input buffer $1.6 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}$	1.5		EVDDO	V
	VIH3	P20 to P27, P150 to P156	0.7V <sub>DD</sub>		VDD	V	
	VIH4	P60 to P63	0.7EVDD0		6.0	V	
	VIH5	P121 to P124, P137, EXCLK, EXCL	0.8Vdd		VDD	V	
Input voltage, low	VIL1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147		0		0.2EV <sub>DD0</sub>	V
	VIL2	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V $\leq$ EV <sub>DD0</sub> $\leq$ 5.5 V	0		0.8	V
		P80, P81, P142, P143	TTL input buffer 3.3 V $\leq$ EV <sub>DD0</sub> $<$ 4.0 V	0		0.5	V
			TTL input buffer 1.6 V ≤ EV <sub>DD0</sub> < 3.3 V	0		0.32	V
	VIL3	P20 to P27, P150 to P156	P20 to P27, P150 to P156			0.3Vdd	V
	VIL4	P60 to P63		0		0.3EVDD0	V
	VIL5	P121 to P124, P137, EXCLK, EXCL	0		0.2VDD	V	

- Caution The maximum value of V<sub>IH</sub> of pins P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 is EV<sub>DD0</sub>, even in the N-ch open-drain mode.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



#### 2.5 Peripheral Functions Characteristics

#### AC Timing Test Points



#### 2.5.1 Serial array unit

#### (1) During communication at same potential (UART mode) (T<sub>A</sub> = -40 to +85°C, 1.6 V $\leq$ EV<sub>DD0</sub> = EV<sub>DD1</sub> $\leq$ V<sub>DD</sub> $\leq$ 5.5 V, Vss = EV<sub>SS0</sub> = EV<sub>SS1</sub> = 0 V)

Parameter	Symbol				h-speed Mode	``	/-speed Mode	``	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 1		2.4 V≤ EV	5.5  V		fMCK/6 Note 2		fмск/6		fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 3}$		5.3		1.3		0.6	Mbps
	1.8 V ≤ E	1.8 V ≤ EV	$T_{\text{DD0}} \leq 5.5 \text{ V}$		fмск/6 Note 2		fмск/6		fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 3}$		5.3		1.3		0.6	Mbps
		1.7 V ≤ EV	$T_{\text{DD0}} \leq 5.5 \text{ V}$		fMCK/6 Note 2		fмск/6 Note 2		fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 3}$		5.3		1.3		0.6	Mbps
		1.6 V ≤ EV	$T_{\text{DD0}} \leq 5.5 \text{ V}$	_	_		fмск/6 Note 2		fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 3}$	_			1.3		0.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The following conditions are required for low voltage interface when  $E_{VDD0} < V_{DD}$ .

 $2.4~V \leq EV_{\text{DD0}}$  < 2.7 V : MAX. 2.6 Mbps

- $1.8~\text{V} \leq \text{EV}_\text{DD0} < 2.4~\text{V}$  : MAX. 1.3 Mbps
- $1.6~V \leq EV_{\text{DD0}} < 1.8~V$  : MAX. 0.6 Mbps
- 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

 $\begin{array}{lll} \text{HS (high-speed main) mode:} & 32 \ \text{MHz} \ (2.7 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V}) \\ & 16 \ \text{MHz} \ (2.4 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V}) \\ \text{LS (low-speed main) mode:} & 8 \ \text{MHz} \ (1.8 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V}) \\ \text{LV (low-voltage main) mode:} & 4 \ \text{MHz} \ (1.6 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V}) \\ \end{array}$ 

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).



Parameter	Symbol		Conditions		speed	high- main) ode		/-speed Mode	voltage	low- e main) ode	Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Recep- tion	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V \end{array}$			fмск/6 Note 1		fмск/6 Note 1		fмск/6 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 4}$		5.3		1.3		0.6	Mbps
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$			fмск/6 Note 1		fмск/6 Note 1		fмск/6 Note 1	bps
				Theoretical value of the maximum transfer rate fмск = fclк <sup>Note 4</sup>		5.3		1.3		0.6	Mbps
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$			fMCK/6 Notes 1 to 3		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
		Theoretical value of the maximum transfer rate fмск = fclк <sup>Note 4</sup>		5.3		1.3		0.6	Mbps		

#### (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2) (T<sub>A</sub> = -40 to +85°C. 1.8 V $\leq$ EV<sub>DD0</sub> = EV<sub>DD1</sub> $\leq$ V<sub>DD</sub> $\leq$ 5.5 V. Vss = EV<sub>SS0</sub> = EV<sub>SS1</sub> = 0 V)

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- **2.** Use it with  $EV_{DD0} \ge V_b$ .
- 3. The following conditions are required for low voltage interface when  $E_{VDD0} < V_{DD}$ .

 $2.4~V \leq EV_{\text{DD0}} < 2.7~V$  : MAX. 2.6 Mbps

 $1.8~V \leq EV_{\text{DD0}} < 2.4~V$  : MAX. 1.3 Mbps

4. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are: HS (high-speed main) mode:  $32 \text{ MHz} (2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V})$ 

	16 MHz (2.4 V $\leq$ VDD $\leq$ 5.5 V)
LS (low-speed main) mode:	8 MHz (1.8 V $\leq$ V_{DD} $\leq$ 5.5 V)

LV (low-voltage main) mode:  $4 \text{ MHz} (1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V})$ 

- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.**  $V_{b}[V]$ : Communication line voltage
  - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
  - 3. fMCK: Serial array unit operation clock frequency

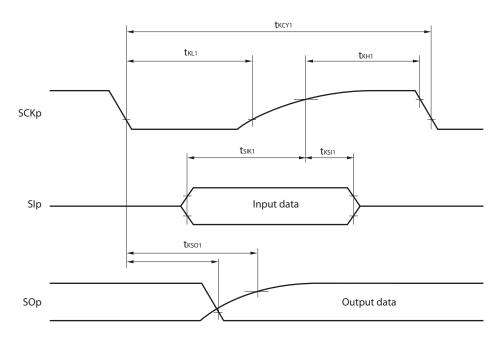
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13)

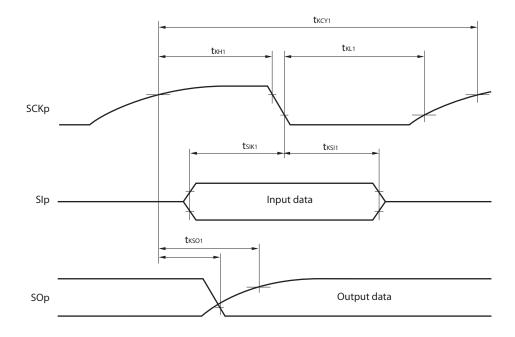
4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



#### CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



- **Remarks 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
  - **2.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.



# (2) When reference voltage (+) = AV<sub>REFP</sub>/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV<sub>REFM</sub>/ANI1 (ADREFM = 1), target pin : ANI16 to ANI26

$(T_{A} = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V},$
Reference voltage (+) = AVREFP, Reference voltage (–) = AVREFM = 0 V)

Parameter	Symbol	Conditions			TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error <sup>Note 1</sup>	AINL	10-bit resolution	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$		1.2	±5.0	LSB
		$EVDD0 = AV_{REFP} = V_{DD}^{Notes 3, 4}$	$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$		1.2	±8.5	LSB
Conversion time	<b>t</b> CONV	10-bit resolution	$3.6~V \le V \text{DD} \le 5.5~V$	2.125		39	μs
		Target ANI pin : ANI16 to	$2.7~V \leq V \text{DD} \leq 5.5~V$	3.1875		39	μS
		ANI26	$1.8~V \leq V \text{DD} \leq 5.5~V$	17		39	μs
			$1.6~V \leq V \text{DD} \leq 5.5~V$	57		95	μs
Zero-scale error <sup>Notes 1, 2</sup>	Ezs 10-bit resolution EVDD0 = AVREFP = VDD Notes 3		$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±0.35	%FSR
		$EVDD0 = AV_{REFP} = V_{DD}$	$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note}}$			±0.60	%FSR
Full-scale error <sup>Notes 1, 2</sup>		10-bit resolution	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±0.35	%FSR
		$EVDD0 = AV_{REFP} = V_{DD}^{Notes 3, 4}$	$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$			±0.60	%FSR
Integral linearity error <sup>Note</sup>	ILE	10-bit resolution	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±3.5	LSB
1	EVDD0 = AVREFP = VDD Notes 3, 4	$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$			±6.0	LSB	
Differential linearity	DLE	10-bit resolution	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±2.0	LSB
error <sup>Note 1</sup>	EVDD0 = AVREFP = VDD	$EVDD0 = AV_{REFP} = V_{DD}^{Notes 3, 4}$	$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$			±2.5	LSB
Analog input voltage	VAIN	ANI16 to ANI26	·	0		AVREFP and EVDD0	V

**Notes 1.** Excludes quantization error ( $\pm 1/2$  LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When AV<sub>REFP</sub> < V<sub>DD</sub>, the MAX. values are as follows. Overall error: Add  $\pm 1.0$  LSB to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>. Zero-scale error/Full-scale error: Add  $\pm 0.05\%$ FSR to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>. Integral linearity error/ Differential linearity error: Add  $\pm 0.5$  LSB to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>.
- 4. When AV<sub>REFP</sub> < EV<sub>DD0</sub> ≤ V<sub>DD</sub>, the MAX. values are as follows. Overall error: Add ±4.0 LSB to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>. Zero-scale error/Full-scale error: Add ±0.20%FSR to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>. Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>.
- 5. When the conversion time is set to 57  $\mu$ s (min.) and 95  $\mu$ s (max.).



#### 3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$ 

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) <sup>Note</sup>	Ceramic resonator/	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	1.0		20.0	MHz
	crystal resonator	$2.4~V \leq V_{\text{DD}} < 2.7~V$	1.0		16.0	MHz
XT1 clock oscillation frequency (fx) <sup>Note</sup>	Crystal resonator		32	32.768	35	kHz

- **Note** Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.
- Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.
- **Remark** When using the X1 oscillator and XT1 oscillator, refer to **5.4 System Clock Oscillator**.

#### 3.2.2 On-chip oscillator characteristics

# $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Oscillators	Parameters		Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency <sup>Notes 1, 2</sup>	fін			1		32	MHz
High-speed on-chip oscillator clock frequency accuracy		–20 to +85 °C	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	-1.0		+1.0	%
		–40 to –20 °C	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	-1.5		+1.5	%
		+85 to +105 °C	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	-2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	fı∟				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

**Notes 1.** High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.



- **Notes 1.** Total current flowing into V<sub>DD</sub> and EV<sub>DD0</sub>, including the input leakage current flowing when the level of the input pin is fixed to V<sub>DD</sub>, EV<sub>DD0</sub> or Vss, EV<sub>SS0</sub>. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
  - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
  - 3. When high-speed system clock and subsystem clock are stopped.
  - 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
  - 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V  $\leq$  V\_DD  $\leq$  5.5 V@1 MHz to 32 MHz

2.4 V 
$$\leq$$
 V<sub>DD</sub>  $\leq$  5.5 V@1 MHz to 16 MHz

- **Remarks 1.** f<sub>MX</sub>: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
  - 2. fin: High-speed on-chip oscillator clock frequency
  - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
  - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C



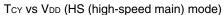
- Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter is in operation.
- 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- 8. Current flowing only during data flash rewrite.
- **9.** Current flowing only during self programming.
- 10. For shift time to the SNOOZE mode, see 18.3.3 SNOOZE mode in the RL78/G13 User's Manual.

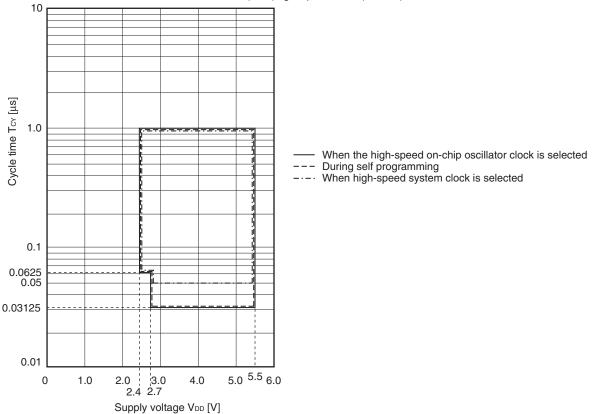
Remarks 1. fil: Low-speed on-chip oscillator clock frequency

- 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- 3. fclk: CPU/peripheral hardware clock frequency
- 4. Temperature condition of the TYP. value is  $T_A = 25^{\circ}C$

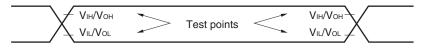


#### Minimum Instruction Execution Time during Main System Clock Operation

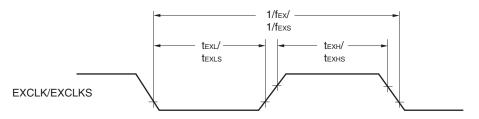




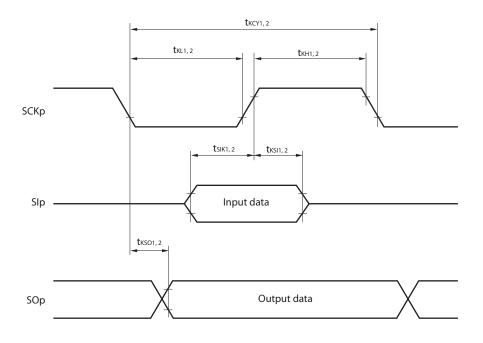
#### **AC Timing Test Points**



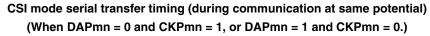
#### External System Clock Timing

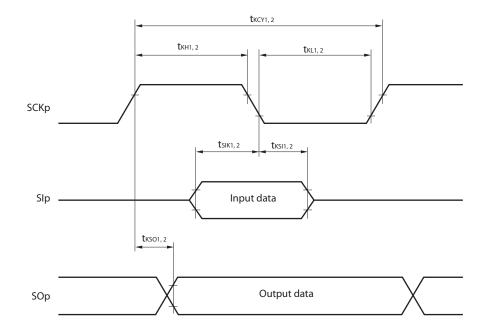






### CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





**Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)

**2.** m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)



Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$		400 Note1	kHz
		$C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$			
		$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V,$		100 Note1	kHz
		$C_b = 100 \text{ pF}, \text{ R}_b = 3  \text{k}\Omega$			
Hold time when SCLr = "L"	t∟ow	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$	1200		ns
		$C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$			
		$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V,$	4600		ns
		$C_b = 100 \text{ pF}, R_b = 3  k\Omega$			
Hold time when SCLr = "H"	tніgн	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$	1200		ns
		$C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$			
		$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V,$	4600		ns
		$C_b = 100 \text{ pF}, \text{ R}_b = 3  \text{k}\Omega$			
Data setup time (reception)	tsu:dat	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$	1/fмск + 220 Note2		ns
		$C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$	Note2		
		$2.4~V \leq EV_{\text{DD}} \leq 5.5~V,$	1/fмск + 580 Note2		ns
		$C_b = 100 \text{ pF}, \text{ R}_b = 3  \text{k}\Omega$	Note2		
Data hold time (transmission)	thd:dat	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$	0	770	ns
		$C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$			
		$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V,$	0	1420	ns
		$C_b = 100 \text{ pF}, \text{ R}_b = 3  \text{k}\Omega$			

#### (4) During communication at same potential (simplified l<sup>2</sup>C mode) (T<sub>A</sub> = -40 to +105°C, 2.4 V $\leq$ EV<sub>DD0</sub> = EV<sub>DD1</sub> $\leq$ V<sub>DD</sub> $\leq$ 5.5 V, Vss = EV<sub>SS0</sub> = EV<sub>SS1</sub> = 0 V)

- Notes 1. The value must also be equal to or less than  $f_{MCK}/4$ .
  - **2.** Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".
- Caution Select the normal input buffer and the N-ch open drain output (V<sub>DD</sub> tolerance (for the 20- to 52-pin products)/EV<sub>DD</sub> tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

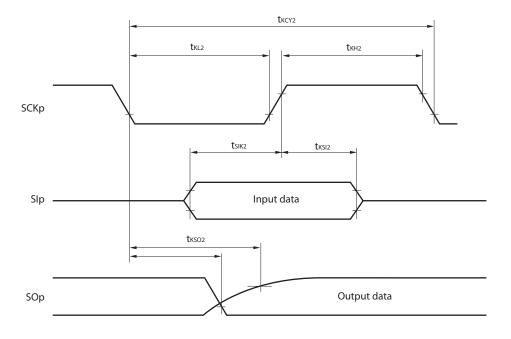


# (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

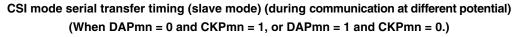
Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	AX.
SCKp cycle time Note 1	<b>t</b> ксү2	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ \text{V}, \end{array}$	24 MHz < fмск	<b>28/f</b> мск		ns
			$20 \text{ MHz} < f_{MCK} \le 24 \text{ MHz}$	<b>24/f</b> мск		ns
		$2.7 V \le V_b \le 4.0 V$	$8 \text{ MHz} < f_{\text{MCK}} \le 20 \text{ MHz}$	<b>20/f</b> мск		ns
			$4 \text{ MHz} < f_{\text{MCK}} \le 8 \text{ MHz}$	<b>16/f</b> мск		ns
			fмск $\leq$ 4 MHz	<b>12/f</b> мск		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \\ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$	24 MHz < fмск	<b>40/f</b> мск		ns
			$20 \text{ MHz} < f_{MCK} \le 24 \text{ MHz}$	<b>32/f</b> мск		ns
			$16 \text{ MHz} < f_{MCK} \le 20 \text{ MHz}$	<b>28/f</b> мск		ns
			$8 \text{ MHz} < f_{\text{MCK}} \le 16 \text{ MHz}$	24/fмск		ns
			$4 \text{ MHz} < f_{\text{MCK}} \le 8 \text{ MHz}$	<b>16/f</b> мск		ns
			fмск $\leq$ 4 MHz	<b>12/f</b> мск		ns
		$2.4 V \le EV_{DD0} < 3.3$ V, $1.6 V \le V_b \le 2.0 V$	24 MHz < fмск	<b>96/f</b> мск		ns
			$20 \text{ MHz} < f_{MCK} \le 24 \text{ MHz}$	<b>72/f</b> мск		ns
			$16 \text{ MHz} < f_{\text{MCK}} \le 20 \text{ MHz}$	<b>64/f</b> мск		ns
			$8 \text{ MHz} < f_{\text{MCK}} \le 16 \text{ MHz}$	<b>52/f</b> мск		ns
			$4 \text{ MHz} < f_{\text{MCK}} \le 8 \text{ MHz}$	<b>32/f</b> мск		ns
			fмск $\leq$ 4 MHz	20/fмск		ns
SCKp high-/low-level tкнг, width tкгг	tкн2, tкL2	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V \end{array}$		tkcy2/2 - 24		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} < 4. \\ 2.3 \ V \leq V_{b} \leq 2.7 \ V \end{array}$		tkcy2/2 - 36		ns
		$\begin{array}{l} 2.4 \; V \leq EV_{\text{DD0}} < 3. \\ 1.6 \; V \leq V_{\text{b}} \leq 2.0 \; V \end{array}$		tkcy2/2 - 100		ns
SIp setup time (to SCKp↑) <sup>Note2</sup> tsiK2	tsik2	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V \end{array}$		1/fмск + 40		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$		1/fмск + 40		ns
		$\begin{array}{l} 2.4 \ V \leq EV_{\text{DD0}} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V \end{array}$		1/fмск + 60		ns
SIp hold time (from SCKp↑) <sup>№te 3</sup>	tksi2			1/fмск + 62		ns
	tkso2	$\begin{array}{l} 4.0 \; V \leq EV_{\text{DD0}} \leq 5.5 \; V,  2.7 \; V \leq V_{\text{b}} \leq 4.0 \; V, \\ C_{\text{b}} = 30 \; pF, \; R_{\text{b}} = 1.4 \; k\Omega \end{array}$			2/fмск + 240	ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq EV_{\text{DD0}} < 4.0 \; V,  2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$			2/fмск + 428	ns
			3 V, 1.6 V $\leq$ Vb $\leq$ 2.0 V		2/fмск + 1146	ns

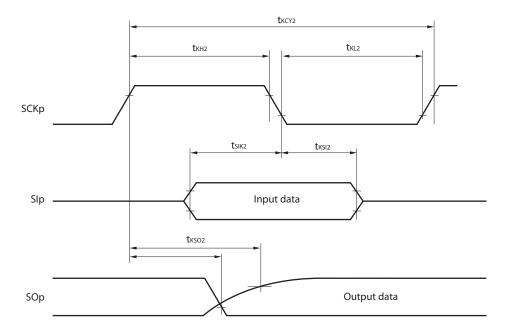
(Notes, Caution and Remarks are listed on the next page.)





CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





**Remarks 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number,

n: Channel number (mn = 00, 01, 02, 10, 12. 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

**2.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.



#### NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.